

# CITATION REPORT

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**High performance continuous wave 1.3 um quantum dot lasers on silicon**

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#	Paper	IF	Citations
265	InGaAs/GaAs quantum well lasers grown on exact GaP/Si (001). <b>2014</b> , 50, 1226-1227		34
264	III-V integration toward electronics and photonics convergence on a silicon platform. <b>2014</b> ,		
263	Quantum dot lasers on silicon. <b>2014</b> ,		1
262	Semiconductor lasers on silicon. <b>2014</b> ,		
261	1.3 $\mu$ m InAs/GaAs Quantum-Dot Laser Monolithically Grown on Si Substrates Using InAlAs/GaAs Dislocation Filter Layers. <b>2014</b> ,		2
260	1.3- $\mu$ m InAs/GaAs quantum-dot lasers monolithically grown on Si substrates using InAlAs/GaAs dislocation filter layers. <i>Optics Express</i> , <b>2014</b> , 22, 11528-35	3.3	94
259	Athermal laser design. <i>Optics Express</i> , <b>2014</b> , 22, 19357-64	3.3	14
258	InAs/GaAs quantum-dot superluminescent diodes monolithically grown on a Ge substrate. <i>Optics Express</i> , <b>2014</b> , 22, 23242-8	3.3	12
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247	Silicon and hybrid silicon photonic devices for intra-datacenter applications: state of the art and perspectives [Invited]. <i>Photonics Research</i> , <b>2015</b> , 3, B10	6	68
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